

ANTREX Electronics

Electronic Components Sourcing Information

Product Reference Information

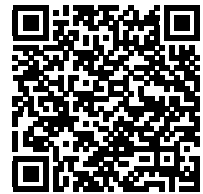
Part Number: IKW40N65RH5XKSA1
Manufacturer: Infineon Technologies
Package: TO-247-3
Availability: Please confirm with sales

Product Page:

<https://antrexco.com/product/details/infineon-technologies/ikw40n65rh5xksa1.html>

Request a Quote:

[Submit RFQ for this part](#)



Scan for product page

Contact Information

Email: info@antrexco.com

WhatsApp: +86-186-8066-5326

Website: <https://antrexco.com>

Quality & Trust

New & Original Components

Supplier verification and packaging condition review

CoC / RoHS / REACH documents available on request

Secure sourcing support for OEM / EMS projects

Note:

This PDF includes an ANTREX product reference cover page.

The original manufacturer datasheet follows from the next page.

CoolSiC™ Hybrid Discrete - TRENCHSTOP™ 5 H5 IGBT co-packed with half-rated 6th generation CoolSiC™ diode

Features

- $V_{CE} = 650\text{ V}$
- $I_C = 40\text{ A}$
- Ultra-low switching losses due to the combination of TRENCHSTOP™ 5 and CoolSiC™ technology
- Benchmark efficiency in hard switching topologies
- Plug-and-play replacement of pure silicon devices
- Maximum junction temperature $T_{vjmax} = 175^\circ\text{C}$
- Qualified according to JEDEC for target applications
- Pb-free lead plating; RoHS compliant
- Complete product spectrum and PSpice Models: <http://www.infineon.com/igbt/>

Potential applications

- Industrial SMPS
- Industrial UPS
- Solar string inverter
- Energy storage
- Charger

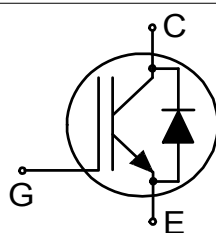
Product validation

- Qualified for applications listed above based on the test conditions in the relevant tests of JEDEC20/22

Description

Package pin definition:

- Pin G - gate
- Pin C & backside - collector
- Pin E - emitter



Type	Package	Marking
IKW40N65RH5	PG-TO247-3	K40ERH5

Table of contents

	Description	1
	Features	1
	Potential applications	1
	Product validation	1
	Table of contents	2
1	Package	3
2	IGBT	3
3	Diode	6
4	Characteristics diagrams	7
5	Package outlines	13
6	Testing conditions	14
	Revision history	15
	Disclaimer	16

1 Package

Table 1 Characteristic values

Parameter	Symbol	Note or test condition	Values			Unit
			Min.	Typ.	Max.	
Internal emitter inductance measured 5 mm (0.197 in.) from case	L_E			13.0		nH
Storage temperature	T_{stg}		-55		150	°C
Soldering temperature		wave soldering 1.6 mm (0.063 in.) from case for 10 s			260	°C
Mounting torque	M	M3 screw Maximum of mounting process: 3			0.6	Nm
Thermal resistance, junction-ambient	$R_{th(j-a)}$				40	K/W

2 IGBT

Table 2 Maximum rated values

Parameter	Symbol	Note or test condition		Values	Unit
Collector-emitter voltage	V_{CE}	$T_{vj} \geq 25\text{ °C}$		650	V
DC collector current, limited by T_{vjmax}	I_C		$T_c = 25\text{ °C}$	74	A
			$T_c = 100\text{ °C}$	46	
Pulsed collector current, t_p limited by T_{vjmax}	I_{Cpulse}			160	A
Turn-off safe operating area		$V_{CE} \leq 650\text{ V}$, $t_p = 1\text{ }\mu\text{s}$, $T_{vj} \leq 175\text{ °C}$		160	A
Gate-emitter voltage	V_{GE}			± 20	V
Transient gate-emitter voltage	V_{GE}	$t_p \leq 10\text{ }\mu\text{s}$, $D < 0.01$		± 30	V
Power dissipation	P_{tot}		$T_c = 25\text{ °C}$	250	W
			$T_c = 100\text{ °C}$	125	

Table 3 Characteristic values

Parameter	Symbol	Note or test condition		Values			Unit
				Min.	Typ.	Max.	
Collector-emitter saturation voltage	V_{CEsat}	$I_C = 40\text{ A}$, $V_{GE} = 15\text{ V}$	$T_{vj} = 25\text{ °C}$		1.65	2.1	V
			$T_{vj} = 125\text{ °C}$		1.85		
			$T_{vj} = 175\text{ °C}$		1.95		
Gate-emitter threshold voltage	V_{GEth}	$I_C = 0.4\text{ mA}$, $V_{CE} = V_{GE}$		3.2	4	4.8	V

(table continues...)

Table 3 (continued) Characteristic values

Parameter	Symbol	Note or test condition		Values			Unit
				Min.	Typ.	Max.	
Zero gate-voltage collector current	I_{CES}	$V_{CE} = 650 \text{ V}, V_{GE} = 0 \text{ V}$	$T_{vj} = 25 \text{ °C}$			600	μA
			$T_{vj} = 175 \text{ °C}$		2000		
Zero gate-voltage collector current	I_{CES}	$V_{CE} = 480 \text{ V}, V_{GE} = 0 \text{ V}$	$T_{vj} = 25 \text{ °C}$			16	μA
Gate-emitter leakage current	I_{GES}	$V_{CE} = 0 \text{ V}, V_{GE} = 20 \text{ V}$				100	nA
Transconductance	g_{fs}	$I_C = 40 \text{ A}, V_{CE} = 20 \text{ V}$			50		S
Input capacitance	C_{ies}	$V_{CE} = 25 \text{ V}, V_{GE} = 0 \text{ V}, f = 250 \text{ kHz}$			2190		pF
Output capacitance	C_{oes}	$V_{CE} = 25 \text{ V}, V_{GE} = 0 \text{ V}, f = 250 \text{ kHz}$			265		pF
Reverse transfer capacitance	C_{res}	$V_{CE} = 25 \text{ V}, V_{GE} = 0 \text{ V}, f = 250 \text{ kHz}$			8		pF
Gate charge	Q_G	$I_C = 40 \text{ A}, V_{GE} = 15 \text{ V}, V_{CC} = 520 \text{ V}$			95		nC
Turn-on delay time	$t_{d(on)}$	$V_{CC} = 400 \text{ V}, V_{GE} = 15 \text{ V}, R_{Gon} = 15 \text{ }\Omega, R_{Goff} = 15 \text{ }\Omega, L_\sigma = 30 \text{ nH}, C_\sigma = 30 \text{ pF}$	$T_{vj} = 25 \text{ °C}, I_C = 20 \text{ A}$		18		ns
			$T_{vj} = 25 \text{ °C}, I_C = 5 \text{ A}$		17		
			$T_{vj} = 150 \text{ °C}, I_C = 20 \text{ A}$		18		
			$T_{vj} = 150 \text{ °C}, I_C = 5 \text{ A}$		17		
Rise time (inductive load)	t_r	$V_{CC} = 400 \text{ V}, V_{GE} = 15 \text{ V}, R_{Gon} = 15 \text{ }\Omega, R_{Goff} = 15 \text{ }\Omega, L_\sigma = 30 \text{ nH}, C_\sigma = 30 \text{ pF}$	$T_{vj} = 25 \text{ °C}, I_C = 20 \text{ A}$		8		ns
			$T_{vj} = 25 \text{ °C}, I_C = 5 \text{ A}$		4		
			$T_{vj} = 150 \text{ °C}, I_C = 20 \text{ A}$		9		
			$T_{vj} = 150 \text{ °C}, I_C = 5 \text{ A}$		4		
Turn-off delay time	$t_{d(off)}$	$V_{CC} = 400 \text{ V}, V_{GE} = 15 \text{ V}, R_{Gon} = 15 \text{ }\Omega, R_{Goff} = 15 \text{ }\Omega, L_\sigma = 30 \text{ nH}, C_\sigma = 30 \text{ pF}$	$T_{vj} = 25 \text{ °C}, I_C = 20 \text{ A}$		165		ns
			$T_{vj} = 25 \text{ °C}, I_C = 5 \text{ A}$		190		
			$T_{vj} = 150 \text{ °C}, I_C = 20 \text{ A}$		195		
			$T_{vj} = 150 \text{ °C}, I_C = 5 \text{ A}$		240		

(table continues...)

Table 3 (continued) Characteristic values

Parameter	Symbol	Note or test condition	Values			Unit
			Min.	Typ.	Max.	
Fall time (inductive load)	t_f	$V_{CC} = 400 \text{ V}, V_{GE} = 15 \text{ V},$ $R_{Gon} = 15 \text{ } \Omega, R_{Goff} = 15 \text{ } \Omega,$ $L_{\sigma} = 30 \text{ nH}, C_{\sigma} = 30 \text{ pF}$	$T_{vj} = 25 \text{ }^{\circ}\text{C},$ $I_C = 20 \text{ A}$	13		ns
			$T_{vj} = 25 \text{ }^{\circ}\text{C}, I_C = 5 \text{ A}$	25		
			$T_{vj} = 150 \text{ }^{\circ}\text{C},$ $I_C = 20 \text{ A}$	22		
			$T_{vj} = 150 \text{ }^{\circ}\text{C},$ $I_C = 5 \text{ A}$	35		
Turn-on energy	E_{on}	$V_{CC} = 400 \text{ V}, V_{GE} = 15 \text{ V},$ $R_{Gon} = 15 \text{ } \Omega, R_{Goff} = 15 \text{ } \Omega,$ $L_{\sigma} = 30 \text{ nH}, C_{\sigma} = 30 \text{ pF}$	$T_{vj} = 25 \text{ }^{\circ}\text{C},$ $I_C = 20 \text{ A}$	0.16		mJ
			$T_{vj} = 25 \text{ }^{\circ}\text{C}, I_C = 5 \text{ A}$	0.03		
			$T_{vj} = 150 \text{ }^{\circ}\text{C},$ $I_C = 20 \text{ A}$	0.18		
			$T_{vj} = 150 \text{ }^{\circ}\text{C},$ $I_C = 5 \text{ A}$	0.05		
Turn-off energy	E_{off}	$V_{CC} = 400 \text{ V}, V_{GE} = 15 \text{ V},$ $R_{Gon} = 15 \text{ } \Omega, R_{Goff} = 15 \text{ } \Omega,$ $L_{\sigma} = 30 \text{ nH}, C_{\sigma} = 30 \text{ pF}$	$T_{vj} = 25 \text{ }^{\circ}\text{C},$ $I_C = 20 \text{ A}$	0.12		mJ
			$T_{vj} = 25 \text{ }^{\circ}\text{C}, I_C = 5 \text{ A}$	0.05		
			$T_{vj} = 150 \text{ }^{\circ}\text{C},$ $I_C = 20 \text{ A}$	0.22		
			$T_{vj} = 150 \text{ }^{\circ}\text{C},$ $I_C = 5 \text{ A}$	0.07		
Total switching energy	E_{ts}	$V_{CC} = 400 \text{ V}, V_{GE} = 15 \text{ V},$ $R_{Gon} = 15 \text{ } \Omega, R_{Goff} = 15 \text{ } \Omega,$ $L_{\sigma} = 30 \text{ nH}, C_{\sigma} = 30 \text{ pF}$	$T_{vj} = 25 \text{ }^{\circ}\text{C},$ $I_C = 20 \text{ A}$	0.28		mJ
			$T_{vj} = 25 \text{ }^{\circ}\text{C}, I_C = 5 \text{ A}$	0.08		
			$T_{vj} = 150 \text{ }^{\circ}\text{C},$ $I_C = 20 \text{ A}$	0.4		
			$T_{vj} = 150 \text{ }^{\circ}\text{C},$ $I_C = 5 \text{ A}$	0.12		
IGBT thermal resistance, junction-case	$R_{th(j-c)}$				0.6	K/W
Operating junction temperature	T_{vj}		-40		175	$^{\circ}\text{C}$

3 Diode

Table 4 Maximum rated values

Parameter	Symbol	Note or test condition		Values	Unit
Repetitive peak reverse voltage	V_{RRM}	$T_{vj} \geq 25\text{ °C}$		650	V
Diode forward current, limited by T_{vjmax}	I_F		$T_c = 25\text{ °C}$	27.5	A
			$T_c = 100\text{ °C}$	18.5	
Diode pulsed current, t_p limited by T_{vjmax} ¹⁾	I_{Fpulse}			60	A

1) Pulse current level depends on T_{vj} of diode chip, see also Fig. "Maximum pulse current as a function of junction temperature"

Table 5 Characteristic values

Parameter	Symbol	Note or test condition		Values			Unit
				Min.	Typ.	Max.	
Diode forward voltage	V_F	$I_F = 16\text{ A}$	$T_{vj} = 25\text{ °C}$		1.35	1.5	V
			$T_{vj} = 125\text{ °C}$		1.55		
			$T_{vj} = 175\text{ °C}$		1.65		
Diode thermal resistance, junction-case	$R_{th(j-c)}$					1.8	K/W
Operating junction temperature	T_{vj}			-40		175	°C

Note: For optimum lifetime and reliability, Infineon recommends operating conditions that do not exceed 80% of the maximum ratings stated in this datasheet.

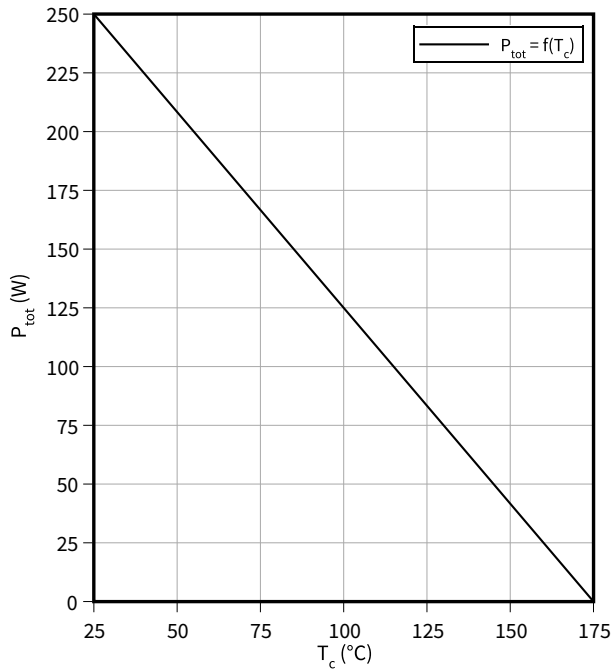
Electrical Characteristic at $T_{vj} = 25\text{ °C}$, unless otherwise specified.

Dynamic test circuit, parasitic inductance L_σ , parasitic capacitor C_σ from Fig. E. Energy losses include "tail" and diode reverse recovery.

4 Characteristics diagrams

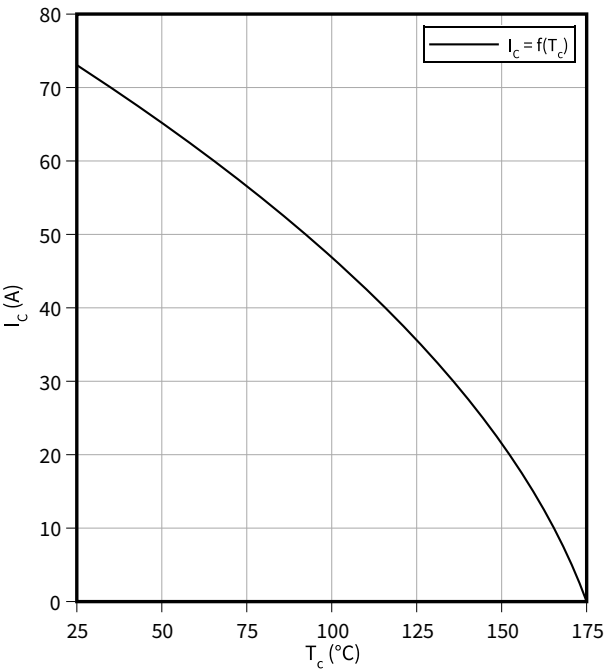
Power dissipation as a function of case temperature

$P_{\text{tot}} = f(T_c)$
 $T_{vj} \leq 175\text{ °C}$



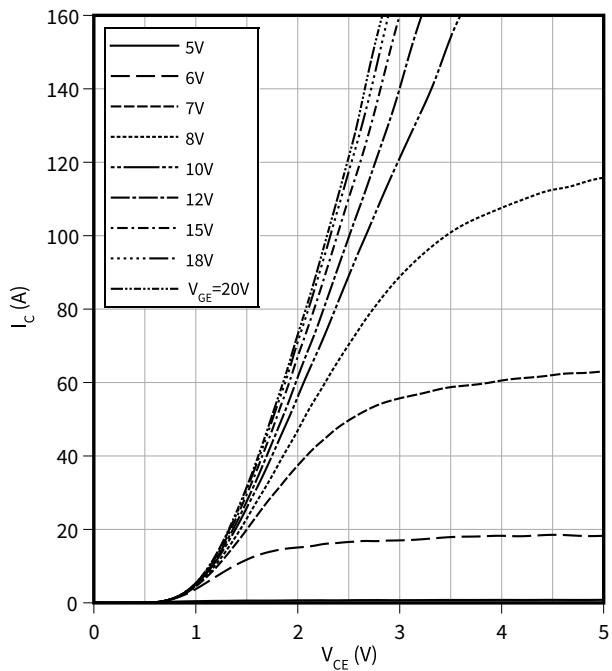
Collector current as a function of case temperature

$I_C = f(T_c)$
 $T_{vj} \leq 175\text{ °C}, V_{GE} \geq 15\text{ V}$



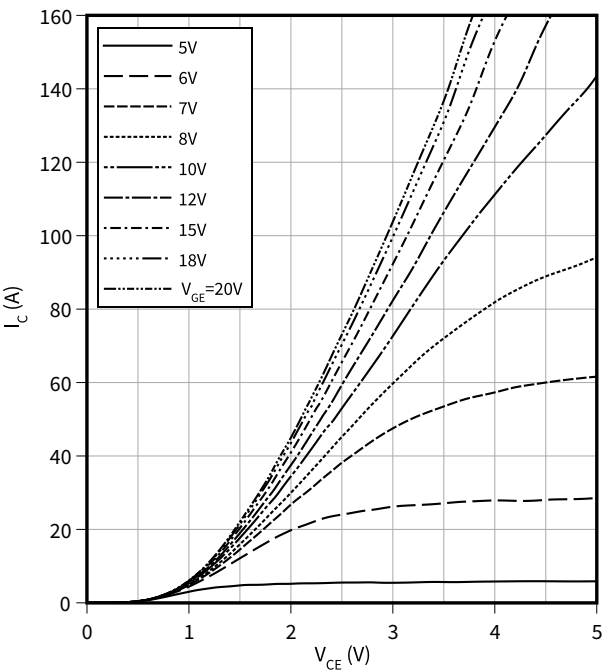
Typical output characteristic

$I_C = f(V_{CE})$
 $T_{vj} = 25\text{ °C}$



Typical output characteristic

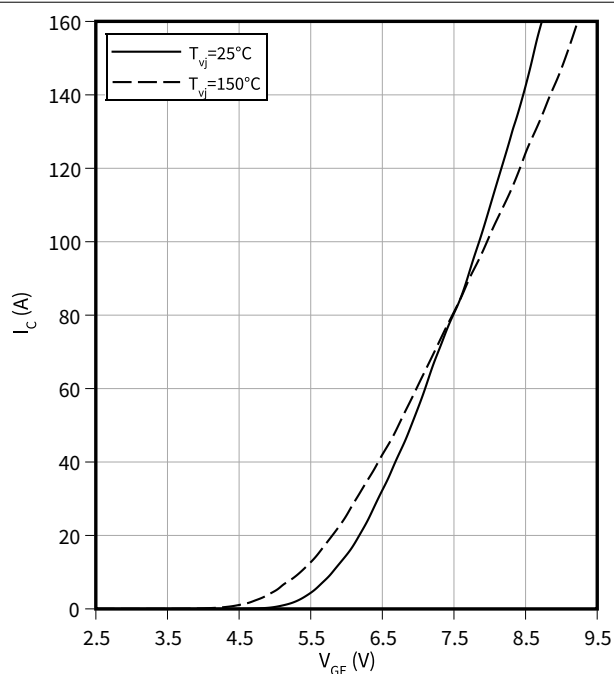
$I_C = f(V_{CE})$
 $T_{vj} = 150\text{ °C}$



Typical transfer characteristic

$$I_C = f(V_{GE})$$

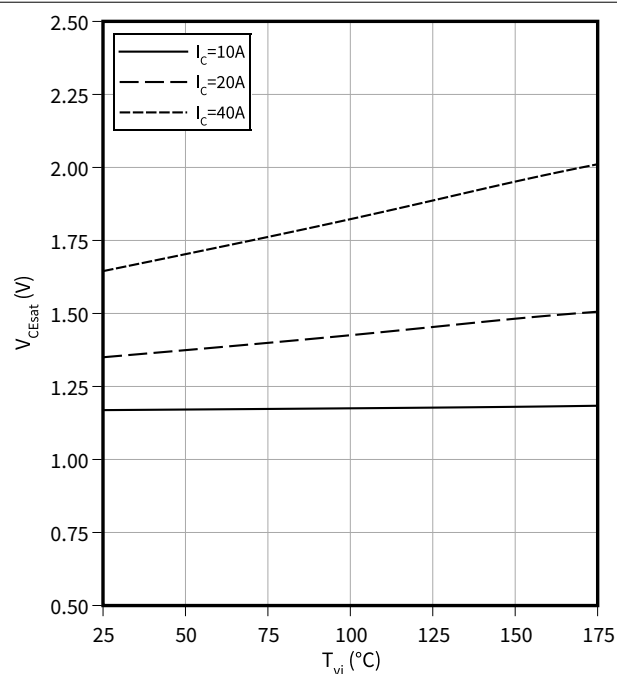
$$V_{CE} = 20 \text{ V}$$



Typical collector-emitter saturation voltage as a function of junction temperature

$$V_{CEsat} = f(T_{vj})$$

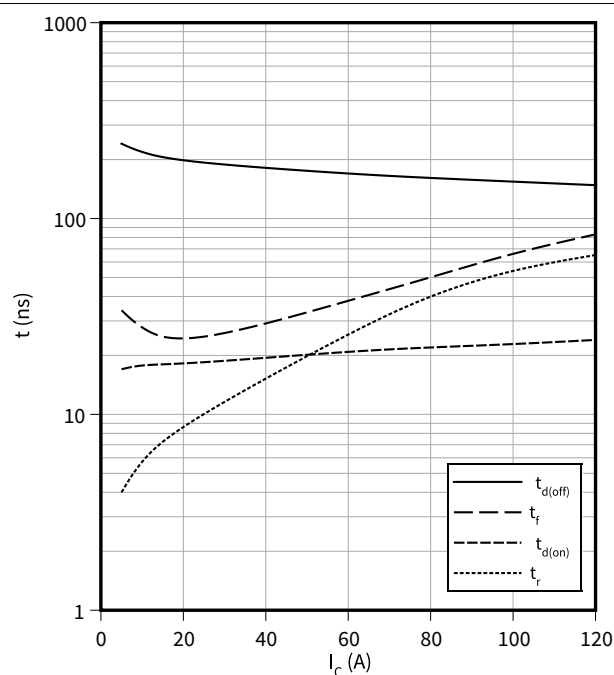
$$V_{GE} = 15 \text{ V}$$



Typical switching times as a function of collector current

$$t = f(I_C)$$

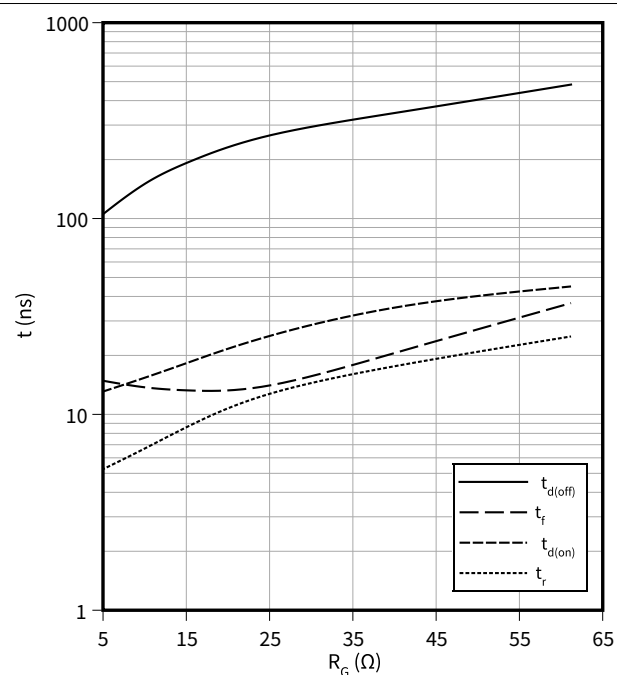
$$V_{CC} = 400 \text{ V}, T_{vj} = 150^\circ\text{C}, V_{GE} = 0/15 \text{ V}, R_G = 15 \Omega$$



Typical switching times as a function of gate resistor

$$t = f(R_G)$$

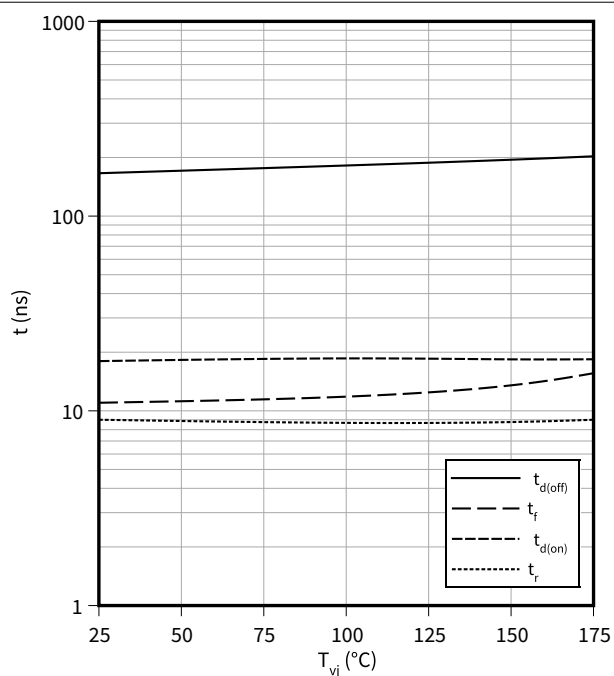
$$I_C = 20 \text{ A}, V_{CC} = 400 \text{ V}, T_{vj} = 150^\circ\text{C}, V_{GE} = 0/15 \text{ V}$$



Typical switching times as a function of junction temperature

$$t = f(T_{vj})$$

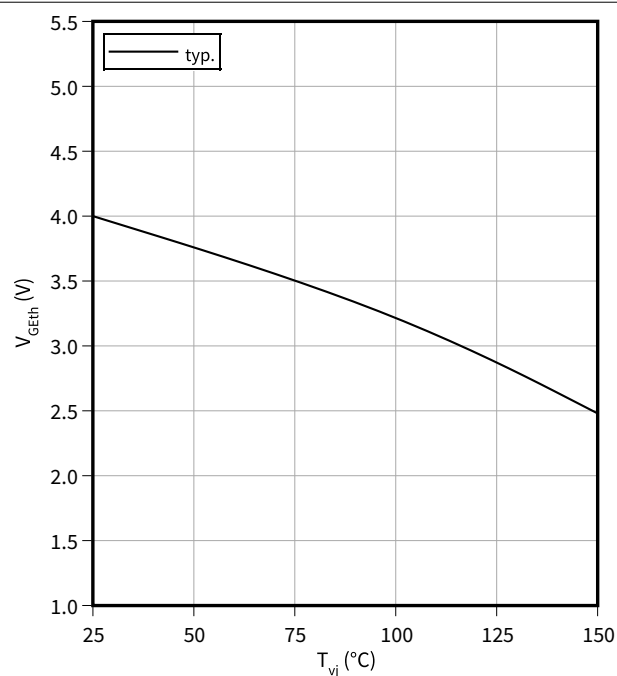
$I_C = 20 \text{ A}$, $V_{CC} = 400 \text{ V}$, $V_{GE} = 0/15 \text{ V}$, $R_G = 15 \Omega$



Gate-emitter threshold voltage as a function of junction temperature

$$V_{GEth} = f(T_{vj})$$

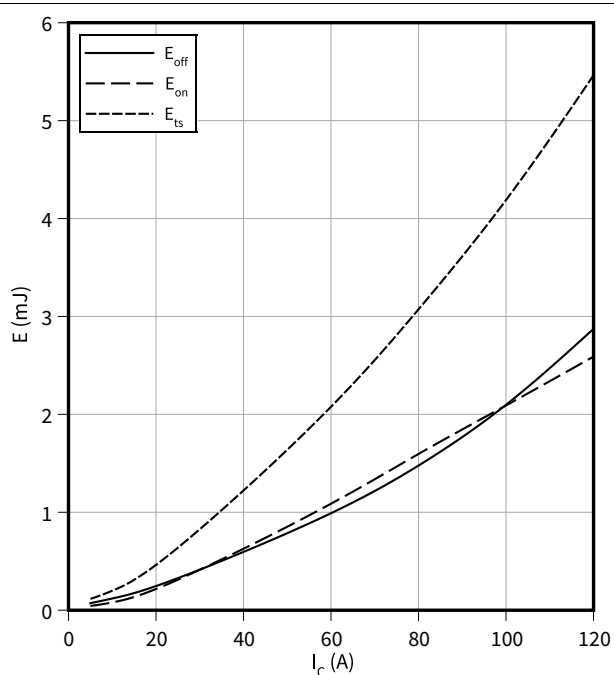
$I_C = 0.4 \text{ mA}$



Typical switching energy losses as a function of collector current

$$E = f(I_C)$$

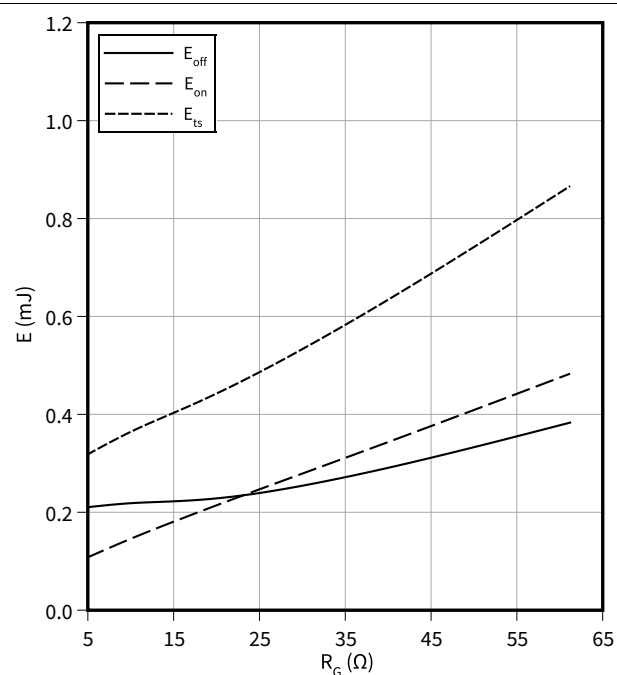
$V_{CC} = 400 \text{ V}$, $T_{vj} = 150 \text{ °C}$, $V_{GE} = 0/15 \text{ V}$, $R_G = 15 \Omega$



Typical switching energy losses as a function of gate resistor

$$E = f(R_G)$$

$I_C = 20 \text{ A}$, $V_{CC} = 400 \text{ V}$, $T_{vj} = 150 \text{ °C}$, $V_{GE} = 0/15 \text{ V}$

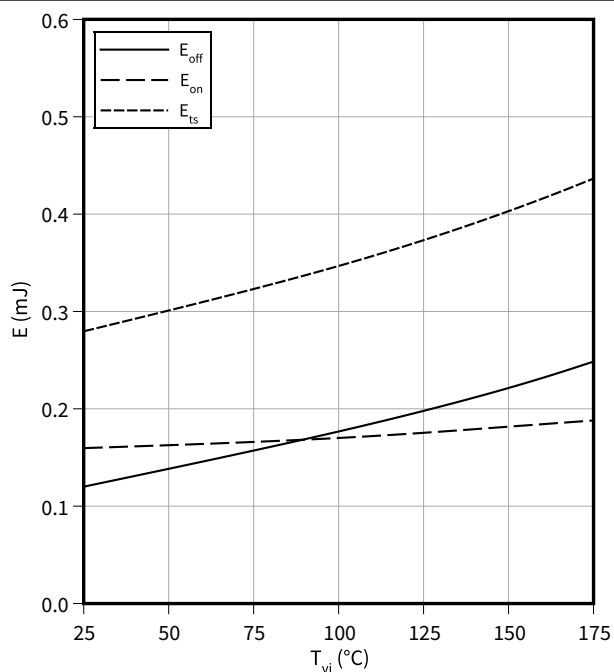


4 Characteristics diagrams

Typical switching energy losses as a function of junction temperature

$$E = f(T_{vj})$$

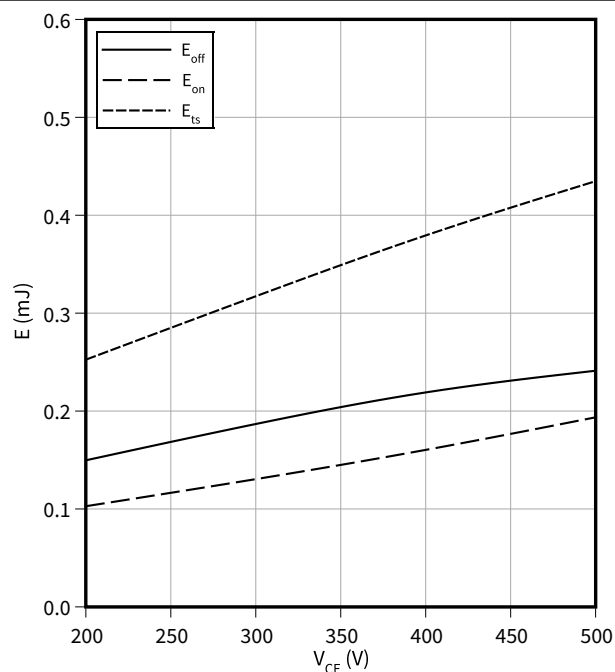
$I_C = 20\text{ A}$, $V_{CC} = 400\text{ V}$, $V_{GE} = 0/15\text{ V}$, $R_G = 15\ \Omega$



Typical switching energy losses as a function of collector emitter voltage

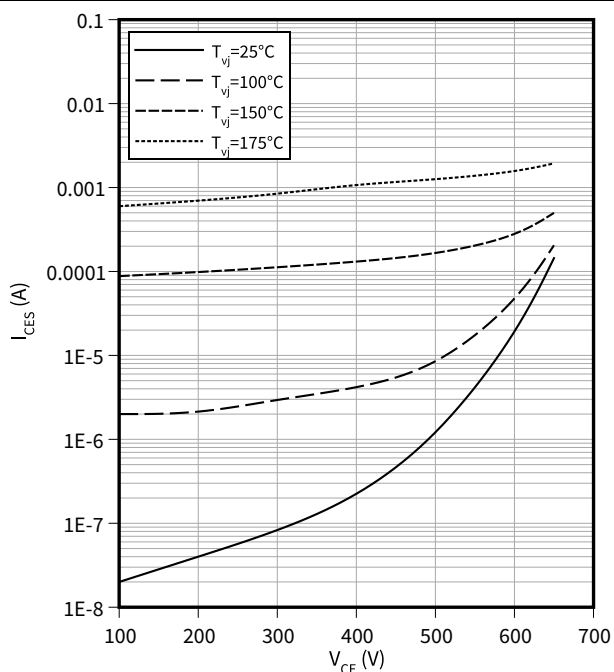
$$E = f(V_{CE})$$

$I_C = 20\text{ A}$, $V_{GE} = 0/15\text{ V}$, $T_{vj} = 150\text{ °C}$, $R_G = 15\ \Omega$



Typ. reverse current vs. reverse voltage as a function of Tvj

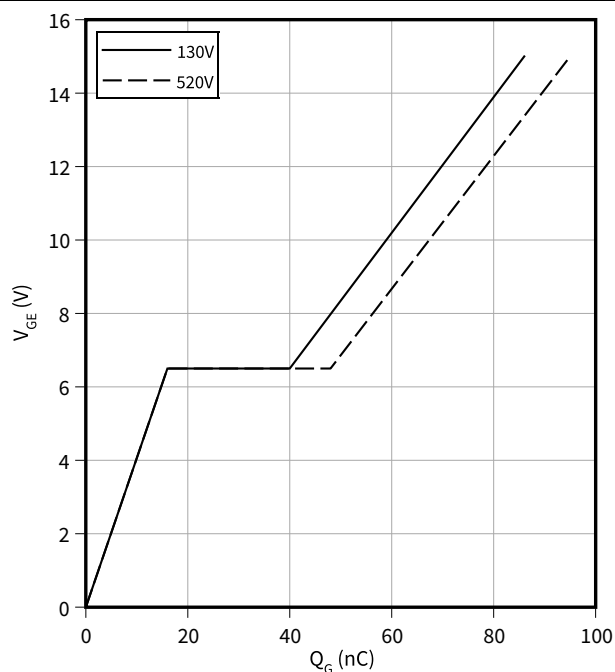
$$I_{CES} = f(V_{CE})$$



Typical gate charge

$$V_{GE} = f(Q_G)$$

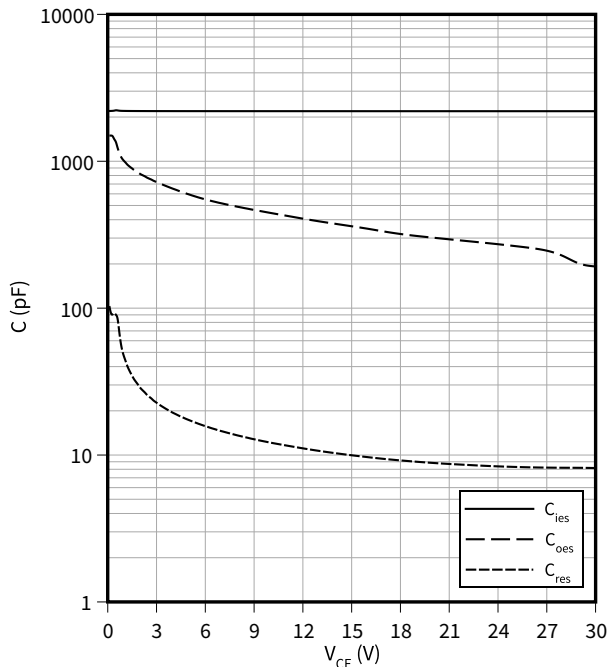
$I_C = 40\text{ A}$



4 Characteristics diagrams

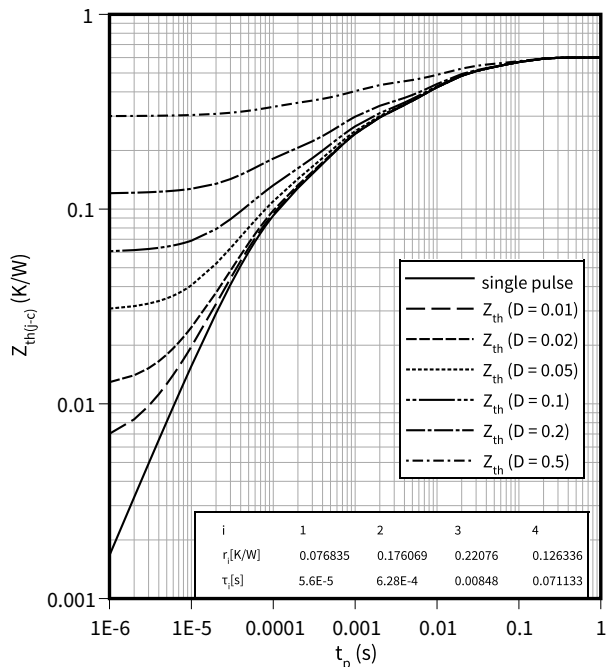
Typical capacitance as a function of collector-emitter voltage

$C = f(V_{CE})$
 $f = 250 \text{ kHz}, V_{GE} = 0 \text{ V}$



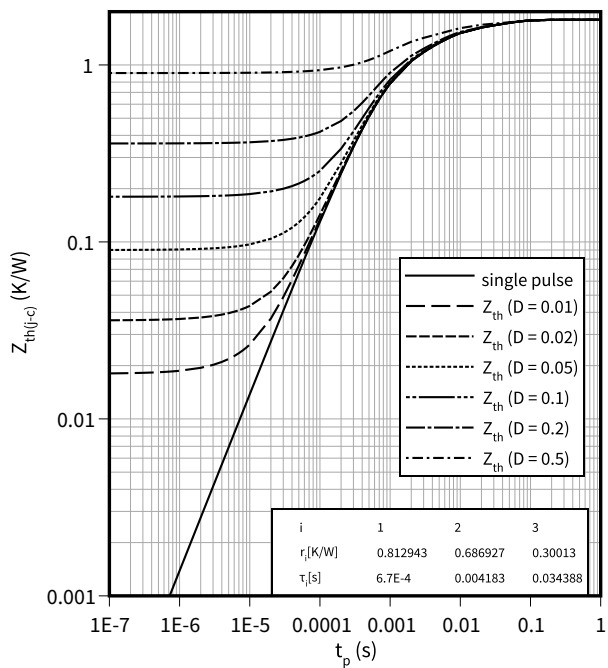
IGBT transient thermal impedance as a function of pulse width

$Z_{th(j-c)} = f(t_p)$
 $D = t_p/T$



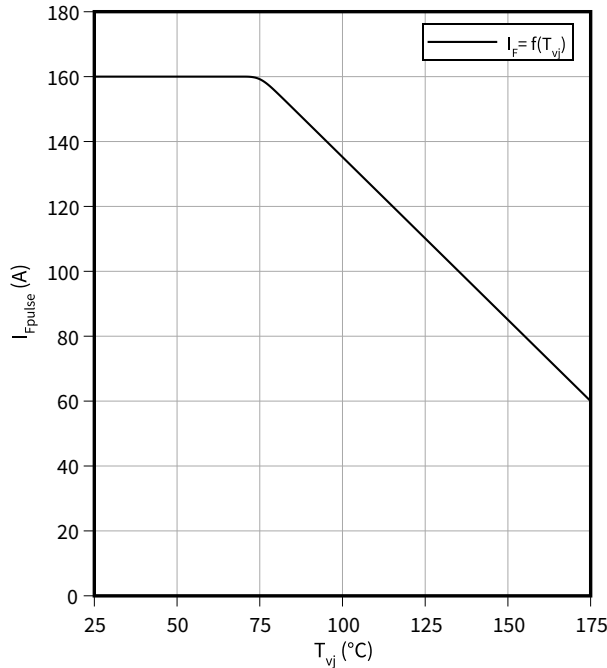
Diode transient thermal impedance as a function of pulse width

$Z_{th(j-c)} = f(t_p)$
 $D = t_p/T$



Maximum pulse current as a function of junction temperature

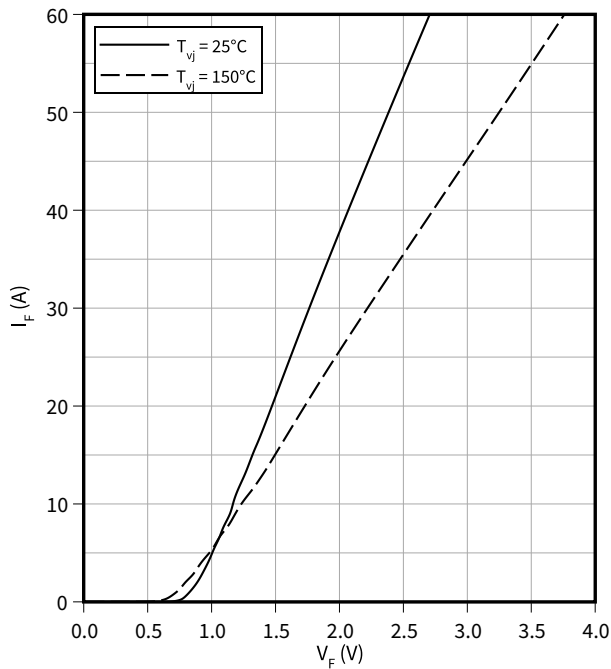
$I_{Fpulse} = f(T_{vj})$



4 Characteristics diagrams

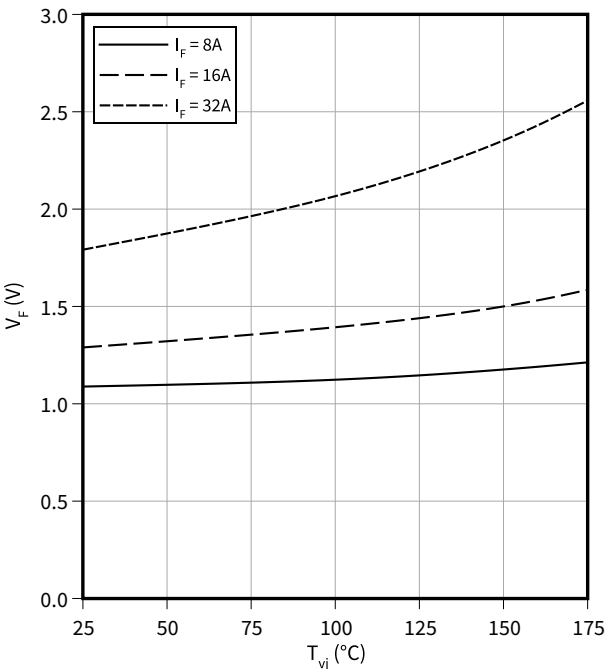
Typical diode forward current as a function of forward voltage

$I_F = f(V_F)$



Typical diode forward voltage as a function of junction temperature

$V_F = f(T_{vj})$



5 Package outlines

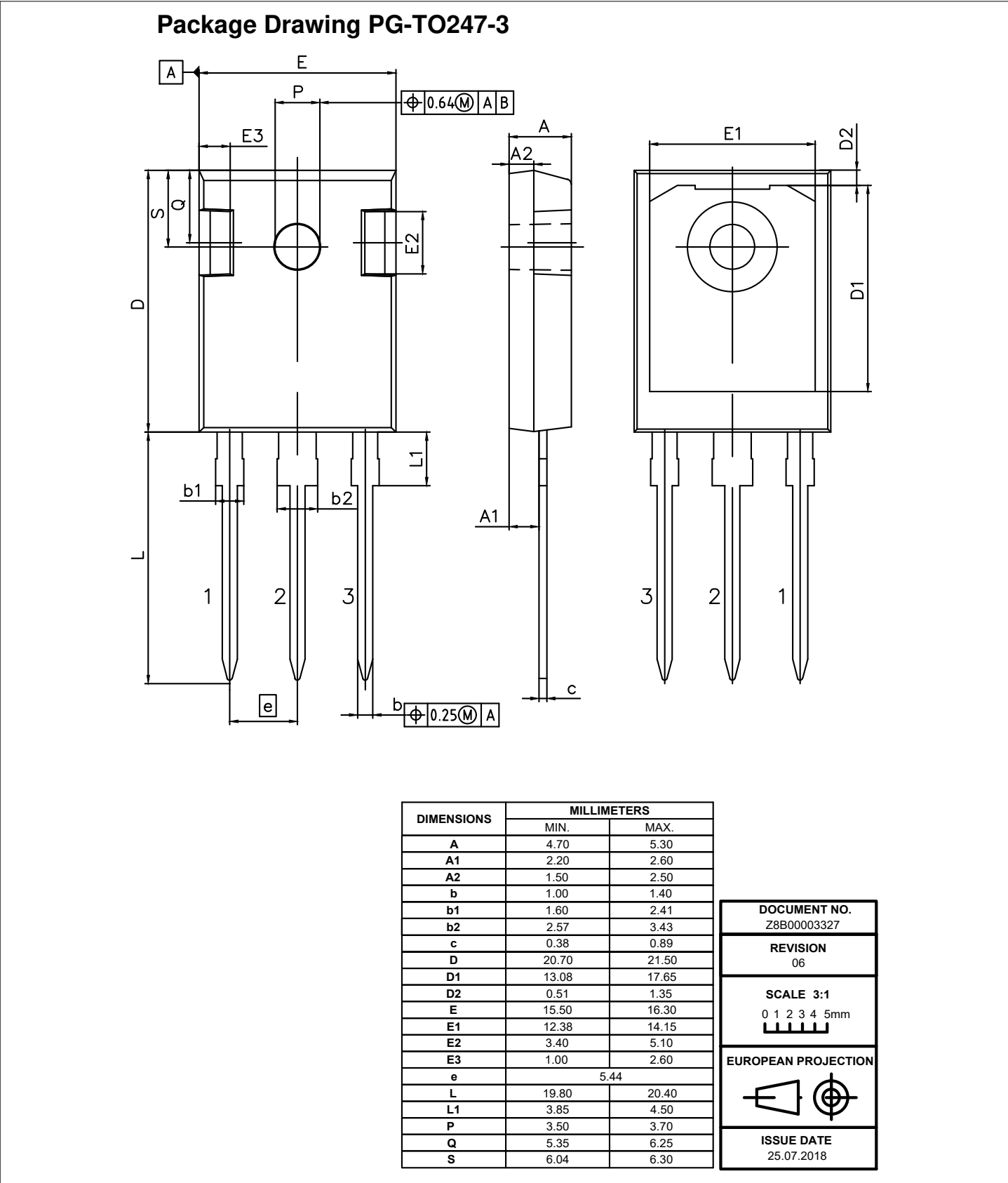


Figure 1

6 Testing conditions

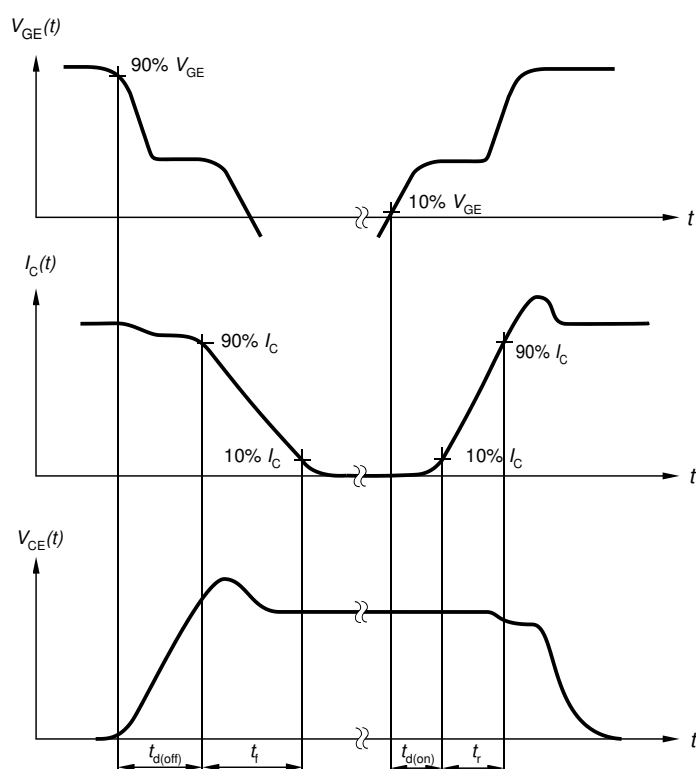


Figure A. Definition of switching times

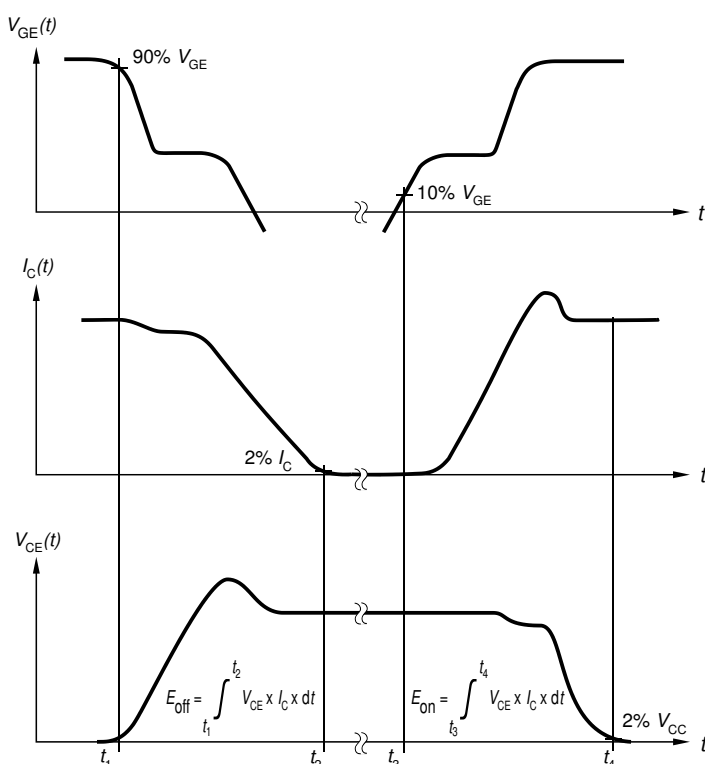


Figure B. Definition of switching losses

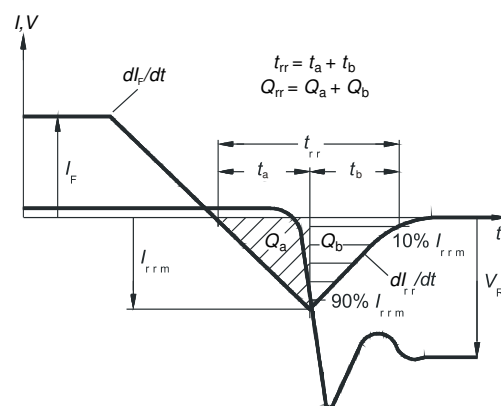


Figure C. Definition of diode switching characteristics

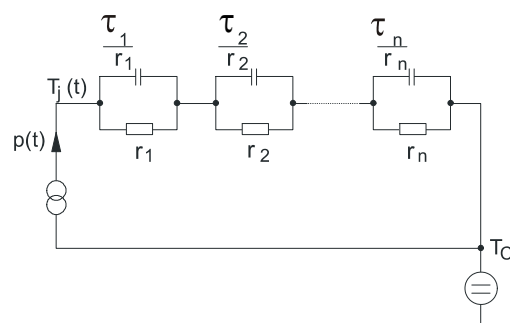


Figure D. Thermal equivalent circuit

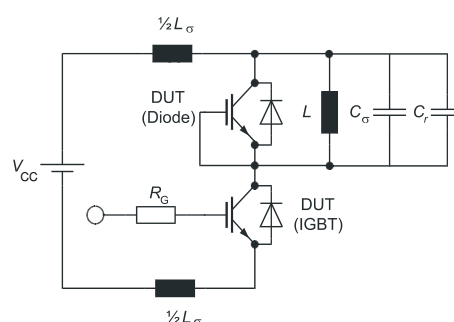


Figure E. **Dynamic test circuit**
Parasitic inductance L_σ ,
parasitic capacitor C_σ ,
relief capacitor C_r ,
(only for ZVT switching)

Revision history

Document revision	Date of release	Description of changes
V1.1	2020-03-20	Preliminary data sheet
V2.1	2020-07-27	Final Data Sheet
n/a	2020-11-30	Datasheet migrated to a new system with a new layout and new revision number schema: target or preliminary datasheet = 0.xy; final datasheet = 1.xy
1.10	2022-09-22	Rename of product family name from “Hybrid CoolSiC™ IGBT” to “CoolSiC™ hybrid discrete”

Trademarks

All referenced product or service names and trademarks are the property of their respective owners.

Edition 2022-09-22

Published by

Infineon Technologies AG
81726 Munich, Germany

© 2022 Infineon Technologies AG
All Rights Reserved.

Do you have a question about any aspect of this document?

Email: erratum@infineon.com

Document reference
IFX-AAL362-003

Important notice

The information given in this document shall in no event be regarded as a guarantee of conditions or characteristics ("Beschaffenhheitsgarantie").

With respect to any examples, hints or any typical values stated herein and/or any information regarding the application of the product, Infineon Technologies hereby disclaims any and all warranties and liabilities of any kind, including without limitation warranties of non-infringement of intellectual property rights of any third party.

In addition, any information given in this document is subject to customer's compliance with its obligations stated in this document and any applicable legal requirements, norms and standards concerning customer's products and any use of the product of Infineon Technologies in customer's applications.

The data contained in this document is exclusively intended for technically trained staff. It is the responsibility of customer's technical departments to evaluate the suitability of the product for the intended application and the completeness of the product information given in this document with respect to such application.

Please note that this product is not qualified according to the AEC Q100 or AEC Q101 documents of the Automotive Electronics Council.

Warnings

Due to technical requirements products may contain dangerous substances. For information on the types in question please contact your nearest Infineon Technologies office.

Except as otherwise explicitly approved by Infineon Technologies in a written document signed by authorized representatives of Infineon Technologies, Infineon Technologies' products may not be used in any applications where a failure of the product or any consequences of the use thereof can reasonably be expected to result in personal injury.